

## CDBDSC5650-G

**Reverse Voltage: 650 V**

**Forward Current: 5 A**

**RoHS Device**



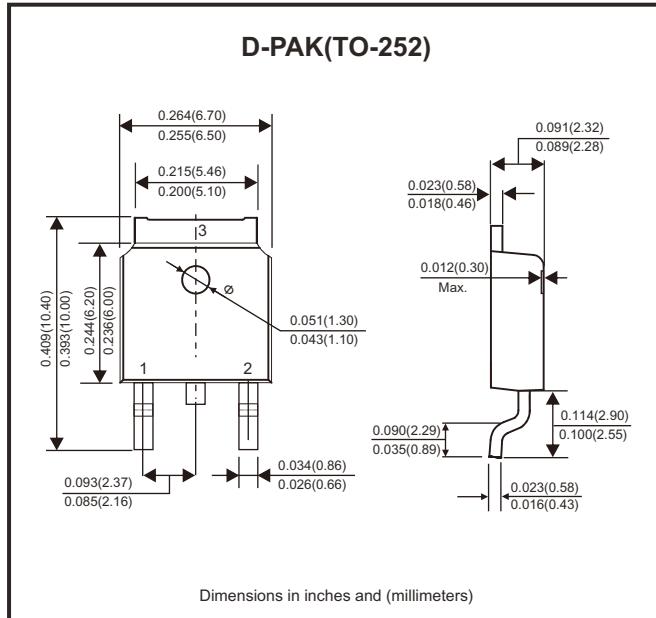
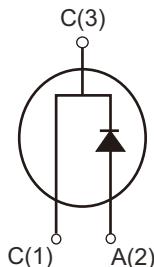
### Features

- Rated to 650V at 5 Amps
- Short recovery time.
- High speed switching possible.
- High frequency operation.
- High temperature operation.
- Temperature independent switching behaviour.
- Positive temperature coefficient on VF.

### Mechanical data

- Case: TO-252/DPAK, molded plastic.
- Terminals: Solderable per MIL-STD-750, method 2026.

### Circuit Diagram



### Maximum Ratings (at TA=25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Value	Unit
Repetitive peak reverse voltage		V <sub>RRM</sub>	650	V
Surge peak reverse voltage		V <sub>RSM</sub>	650	V
DC blocking voltage		V <sub>DC</sub>	650	V
Typical continuous forward current	T <sub>c</sub> = 160°C	I <sub>F</sub>	5	A
Repetitive peak forward surge current	T <sub>c</sub> = 25°C, tp = 10ms Half sine wave, D = 0.3	I <sub>FRM</sub>	40	A
Non-repetitive peak forward surge current	T <sub>c</sub> = 25°C, tp = 10ms Half sine wave	I <sub>FSM</sub>	80	A
Power dissipation	T <sub>c</sub> = 25°C	P <sub>TOT</sub>	85.8	W
	T <sub>c</sub> = 110°C		37.2	
Typical thermal resistance	Junction to case	R <sub>θJC</sub>	1.748	°C/W
Operating junction temperature range		T <sub>J</sub>	-55 ~ +175	°C
Storage temperature range		T <sub>STG</sub>	-55 ~ +175	°C

# Silicon Carbide Power Schottky Diode

**Comchip**  
SMD Diode Specialist

## Electrical Characteristics (at $T_A=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 5\text{A}, T_J = 25^\circ\text{C}$	$V_F$		1.35	1.7	V
	$I_F = 5\text{A}, T_J = 175^\circ\text{C}$			1.55		
Reverse current	$V_R = 650\text{V}, T_J = 25^\circ\text{C}$	$I_R$		10	100	$\mu\text{A}$
	$V_R = 650\text{V}, T_J = 175^\circ\text{C}$			15		
Total capacitive charge	$V_R = 400\text{V}, T_J = 150^\circ\text{C}$ $Q_c = \int_0^{V_R} C(V) dV$	$Q_c$		23		nC
Total capacitance	$V_R = 0\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$	C		430		pF
	$V_R = 200\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$			44		
	$V_R = 400\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$			42.5		

## Rating and Characteristic Curves (CDBDSC5650-G)

Fig.1 - Forward Characteristics

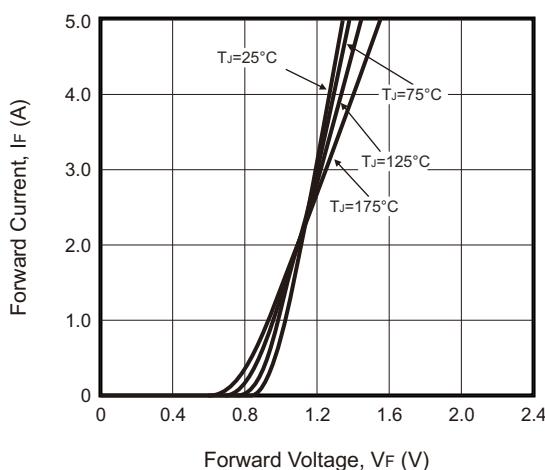


Fig.2 - Reverse Characteristics

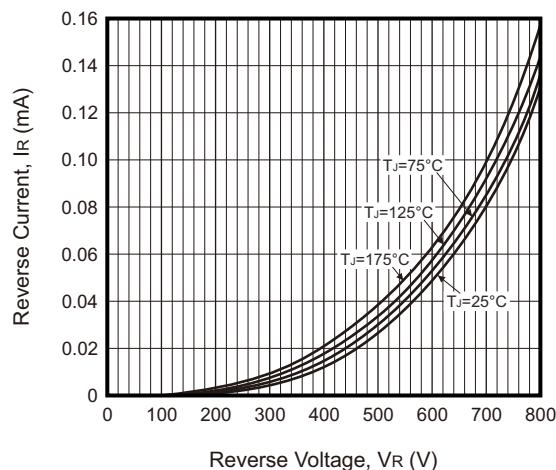


Fig.3 - Current Derating

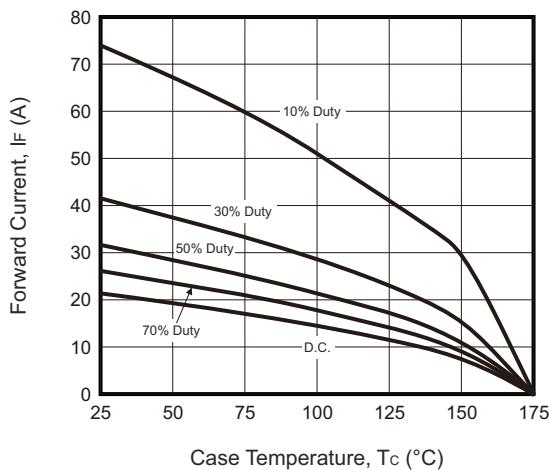
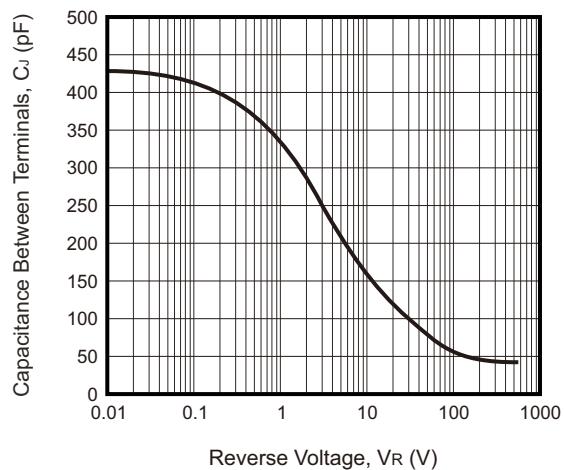
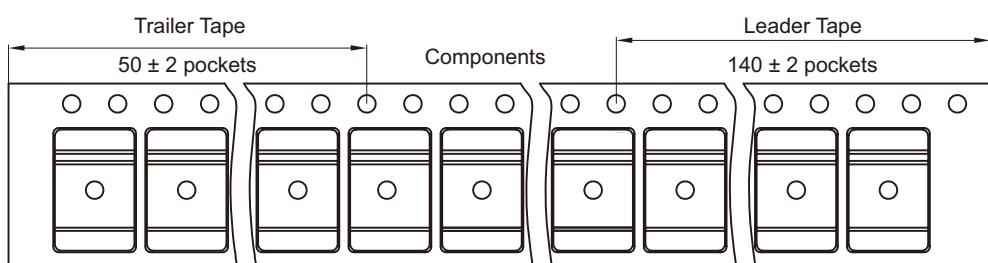
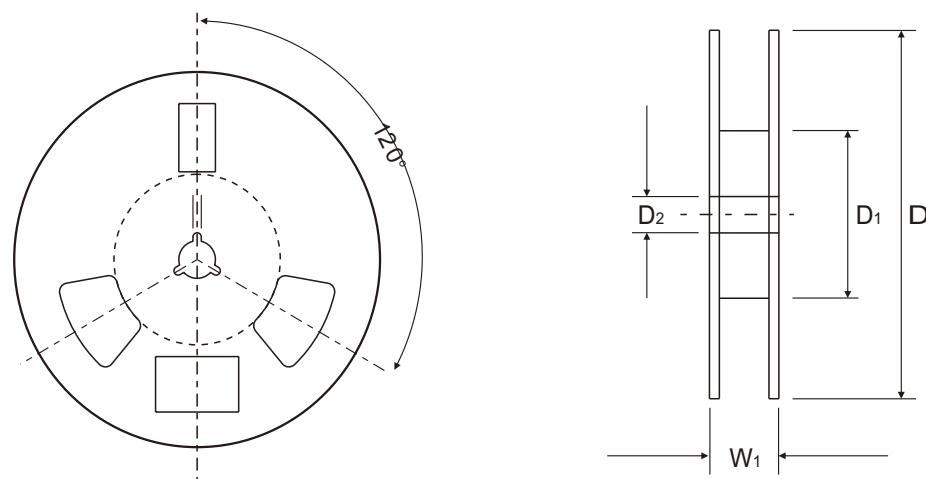
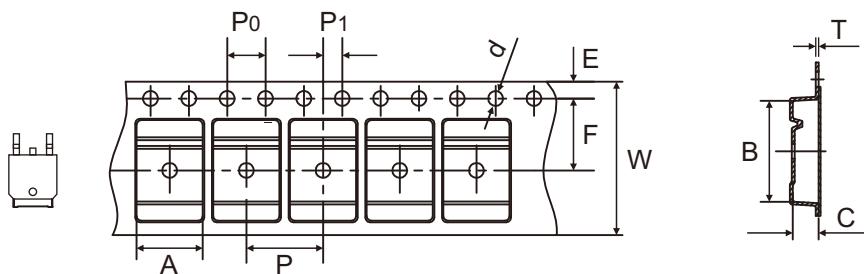


Fig.4 - Capacitance vs. Reverse Voltage



## Reel Taping Specification

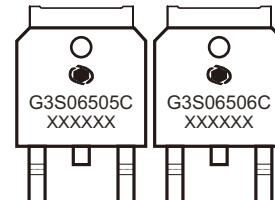
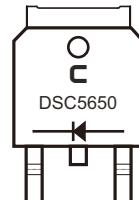


TO-252 (D-PAK)	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	6.90 ± 0.10	10.50 ± 0.10	2.70 ± 0.10	1.55 ± 0.05	332 Max	100.00 ± 2.00	13.00 Min
	(inch)	0.272 ± 0.004	0.413 ± 0.004	0.106 ± 0.004	0.061 ± 0.002	13.071 Max	3.937 ± 0.079	0.512 Min

TO-252 (D-PAK)	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	7.50 ± 0.10	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.30 ± 0.05	16.00 ± 0.10	22.4 Max
	(inch)	0.069 ± 0.004	0.295 ± 0.004	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.012 ± 0.002	0.630 ± 0.004	0.882 Max

## Marking Code

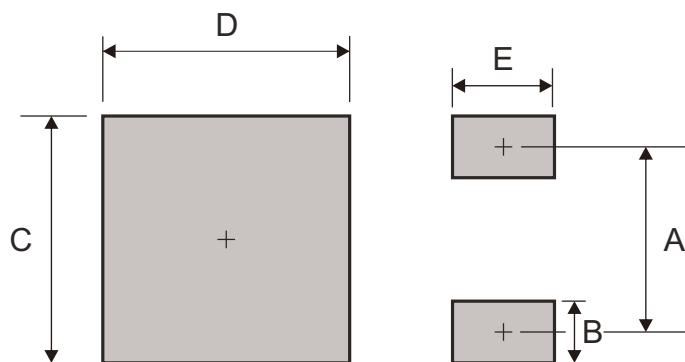
Part Number	Marking Code
CDBDSC5650-G	DSC5650
	G3S06505C
	G3S06506C



C = Comchip Logo      xxxxxx = Control code

## Suggested P.C.B. PAD Layout

SIZE	TO-252 / DPAK	
	(mm)	(inch)
A	4.57	0.180
B	1.20	0.047
C	5.80	0.228
D	5.85	0.230
E	2.00	0.079



## Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	REEL SIZE (inch)
TO-252/D-PAK	2,500	13